

005250-5684560

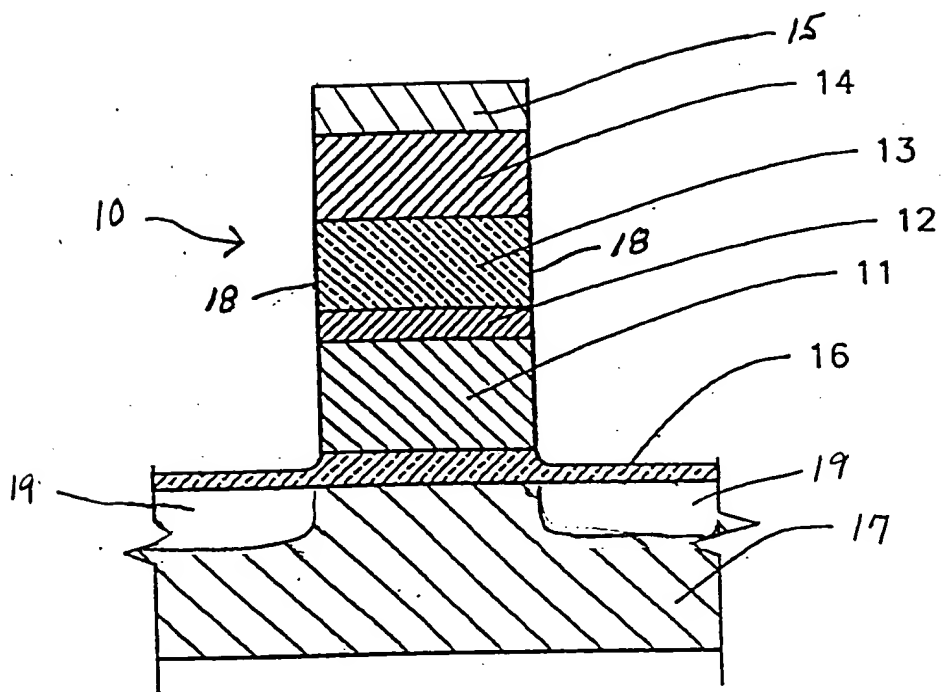


FIG. 1

005550-5664560

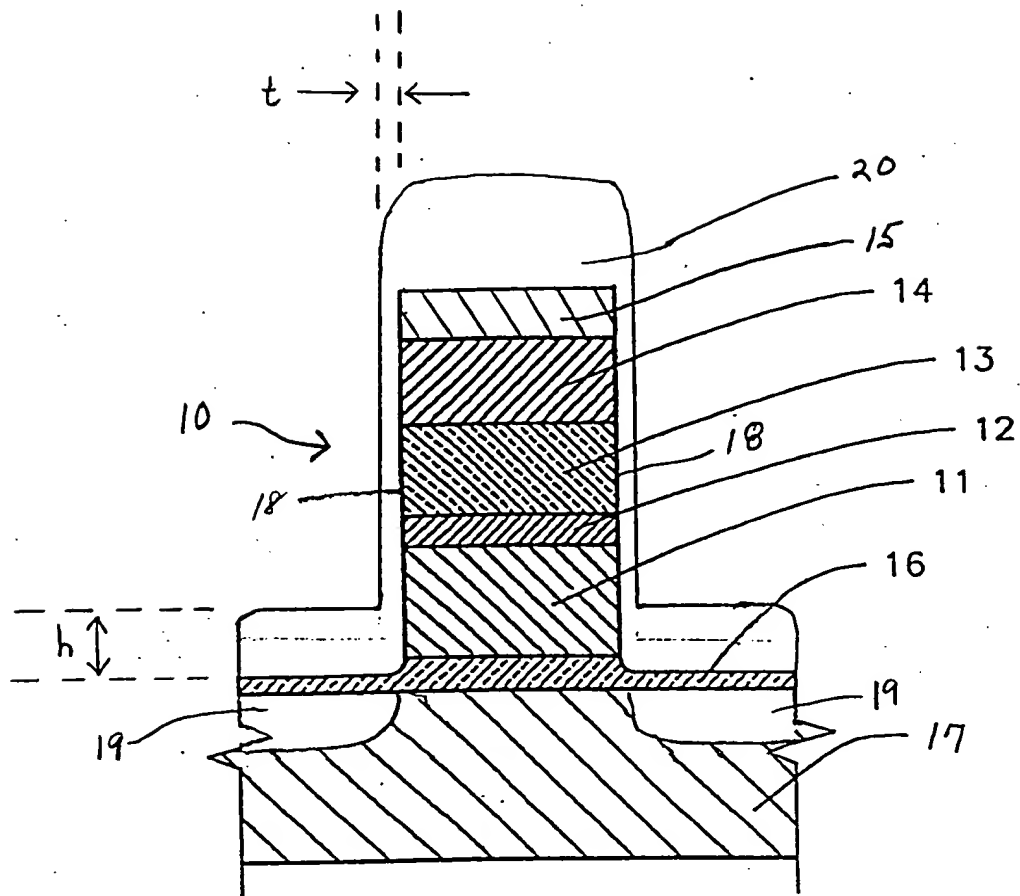


FIG. 2

005250-5622560

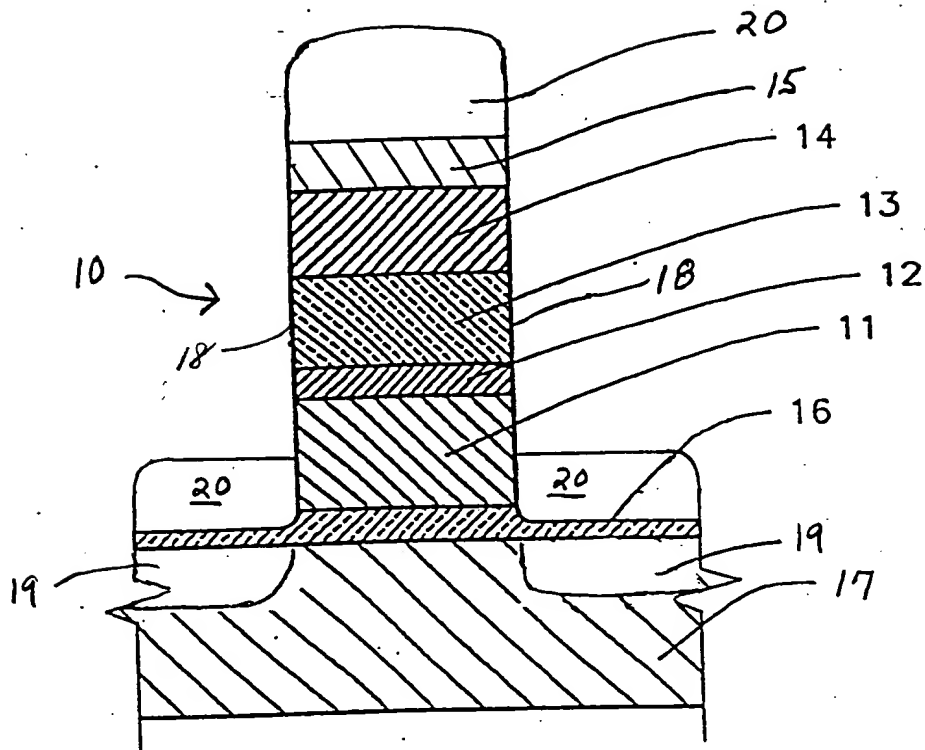


FIG. 3

005250-9284960

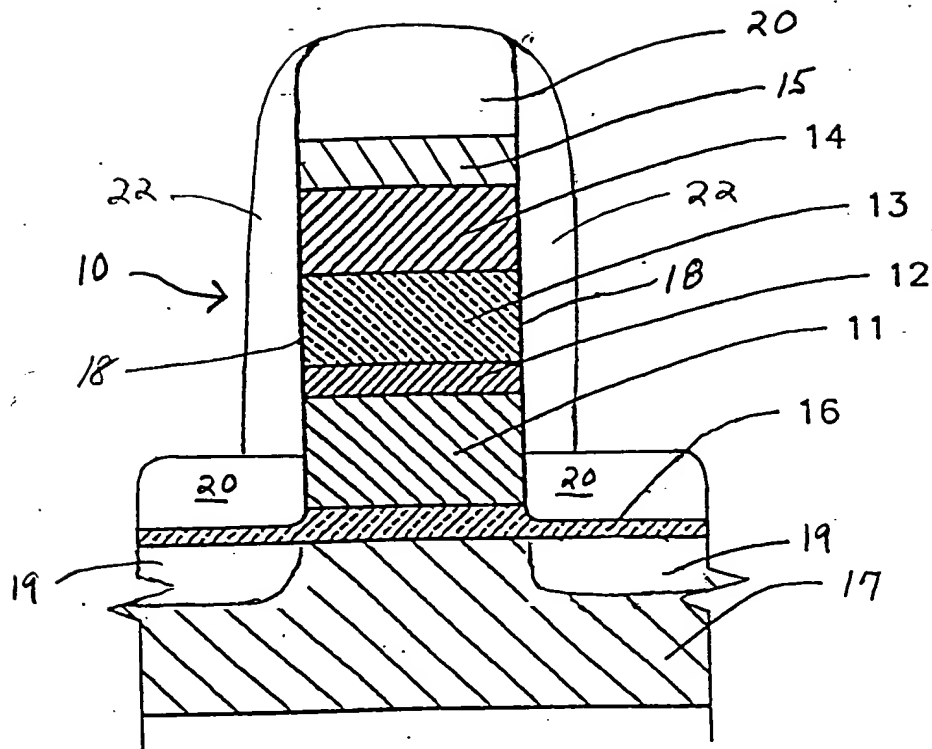


FIG. 4

005250 5684560

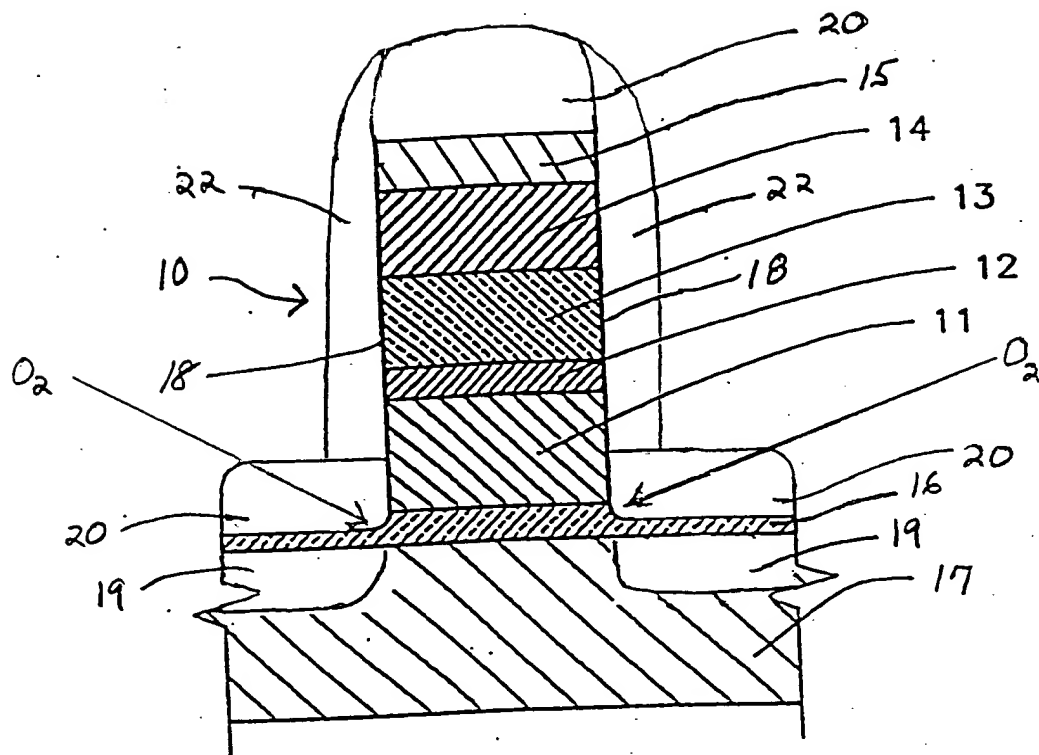


FIG. 5

009250-5284560

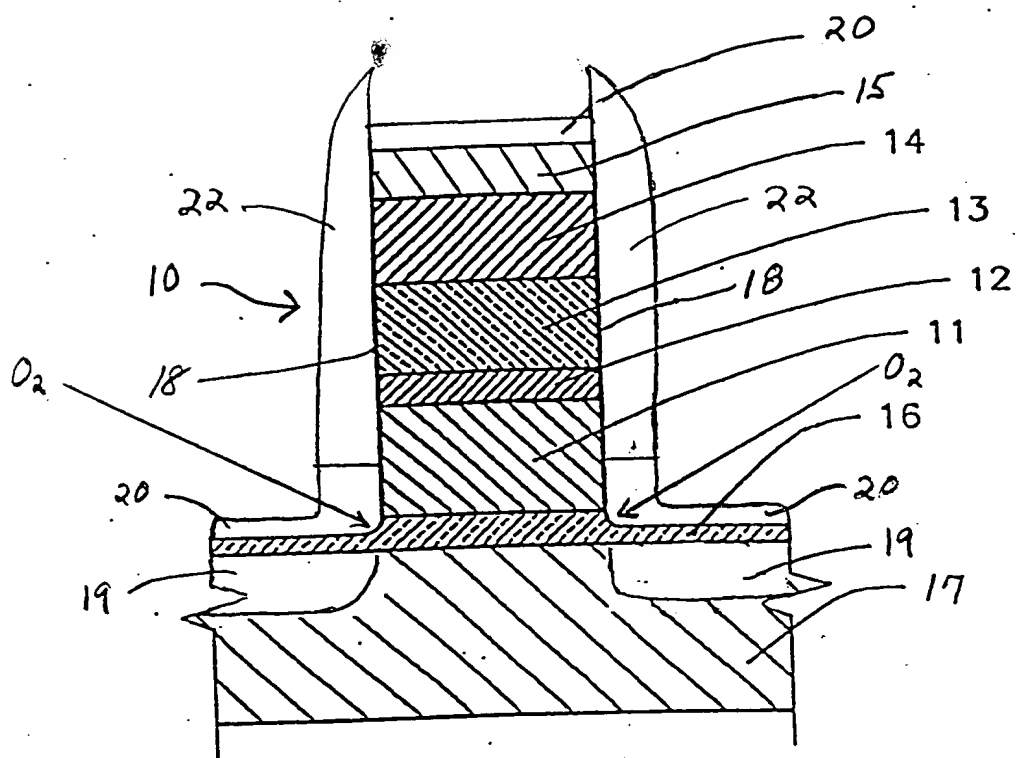


FIG. 6

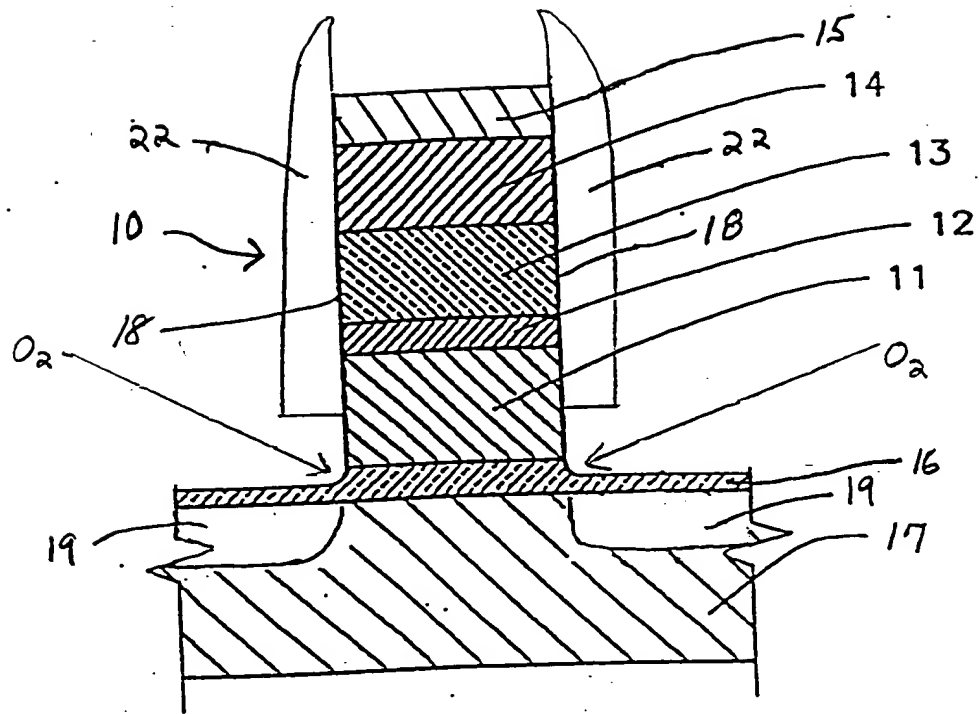


FIG. 7

FIG. 8

005250-5604560

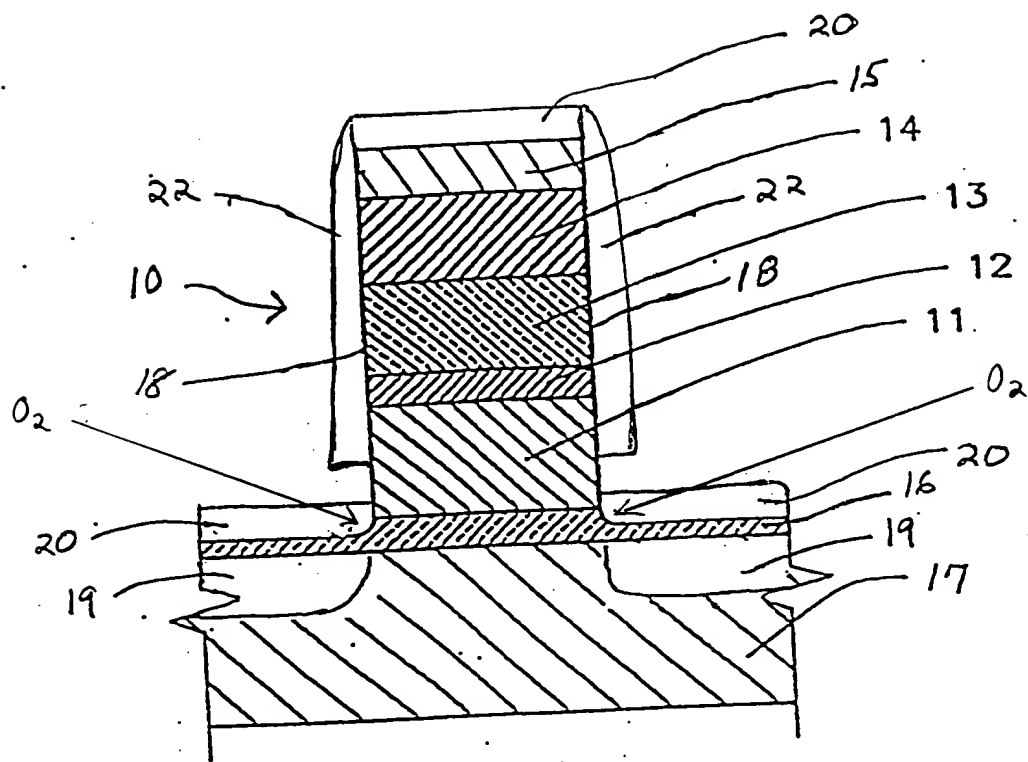


FIG. 9

FORM GATE DIELECTRIC ON UPPER SURFACE OF
SUBSTRATE



FORM WORD LINE STACK WITH CONDUCTIVE BARRIER
AND/OR METAL LAYERS OVER GATE DIELECTRIC



FORM OXIDE LAYER OVER SURFACE OF WAFER



OPTIONALLY REMOVE THIN OXIDE LAYER FROM
SIDEWALLS OF WORD LINE STACK



FORM NITRIDE SPACERS ALONG SIDEWALLS/EDGES OF
BARRIER LAYER AND METAL LAYER OF WORD LINE
STACK



OPTIONALLY REMOVE PART OR ALL OF THE OXIDE LAYER FROM
SURFACE OF WAFER



PERFORM SOURCE/DRAIN REOXIDATION

FIG. 10

005250 5662560

0057036-05500

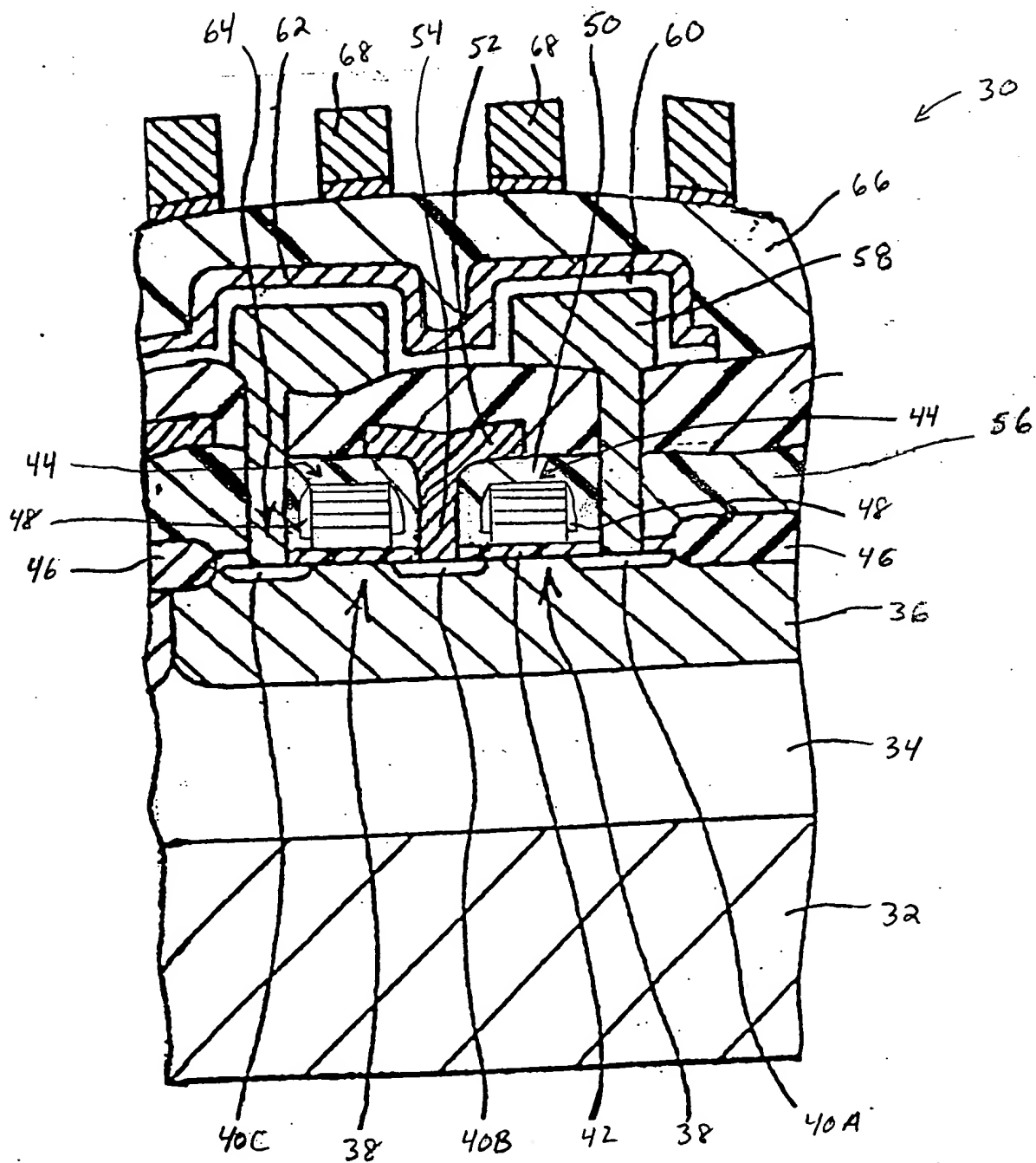


FIG. 11